Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	54	(doped near well or doped-well) and (wafer or substrate) and (metal near oxide) and (polarity).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 19:32
L2	40	(doped-well or doped near well) with (polarity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 19:15
L3	20	2 and (n-type or p-type)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 19:15
L4	183	(doped near well or doped-well) and (wafer or substrate) and (metal near oxide) and (polarity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 19:33
L5	853	(doped near well or doped-well) and (wafer or substrate) and (metal near oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 19:33
L6	26	5 and (third) near3 (doped-well or doped near well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 19:35
L7	17	5 and (third) near (doped-well or doped near well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 19:35

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(p-metal near oxide) near15 (transistor) near25 (doped-well or doped near well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 21:28
L2	33	(metal near oxide) near15 (transistor) near25 (doped-well or doped near well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 21:29
L3	9	(metal near oxide) near15 (transistor) near25 (n) near (doped-well or doped near well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 21:29